74LVTN16245B

3.3 V 16-bit transceiver; 3-state

Rev. 3 — 15 June 2011

Product data sheet

1. **General description**

The 74LVTN16245B is a high-performance BiCMOS product designed for V_{CC} operation at 3.3 V.

This device is a 16-bit transceiver featuring non-inverting 3-state bus compatible outputs in both send and receive directions. The control function implementation minimizes external timing requirements. The device features an output enable input (nOE) for easy cascading and a direction input (nDIR) for direction control.

2. Features and benefits

- 16-bit bus interface
- 3-state buffers
- Output capability: +64 mA and -32 mA
- TTL input and output switching levels
- Input and output interface capability to systems at 5 V supply
- Power-up 3-state
- Live insertion and extraction permitted
- No bus current loading when output is tied to 5 V bus
- Latch-up protection
 - ◆ JESD78B Class II exceeds 500 mA
- ESD protection:
 - HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V

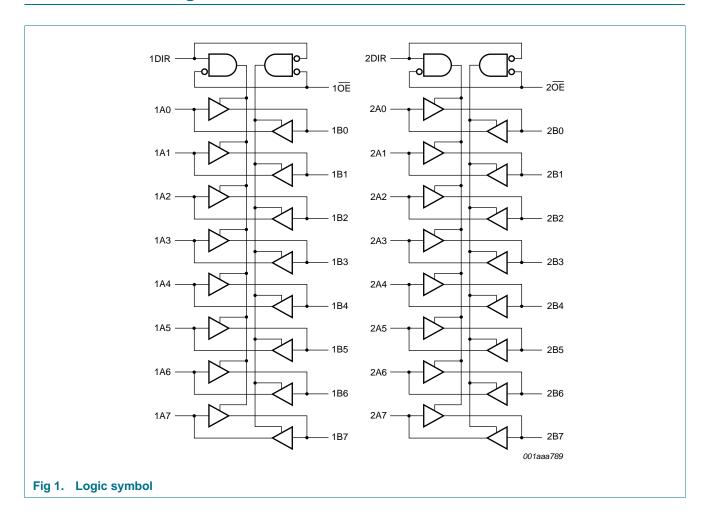
3. Ordering information

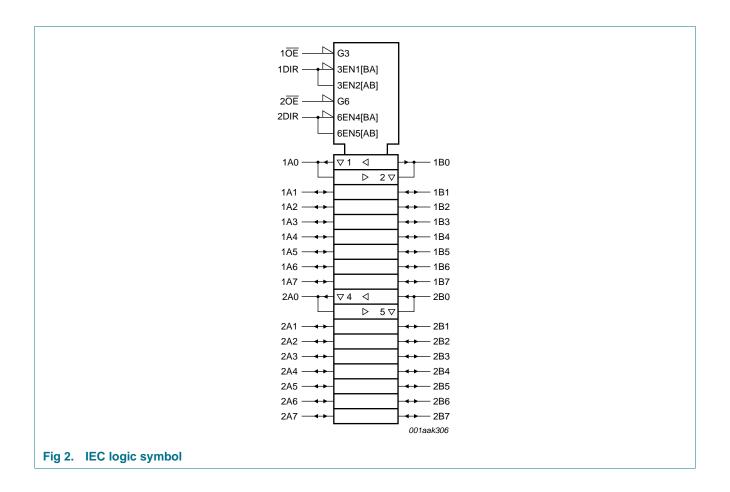
Table 1. **Ordering information**

Type number	Package									
	Temperature range	Name	Description	Version						
74LVTN16245BDGG	–40 °C to +85 °C	TSSOP48	plastic thin shrink small outline package; 48 leads; body width 6.1 mm	SOT362-1						
74LVTN16245BBX	–40 °C to +85 °C	HXQFN60U	plastic thermal enhanced extremely thin quad flat package; no leads; 60 terminals; UTLP based; body $4\times6\times0.5~\text{mm}$	SOT1134-1						



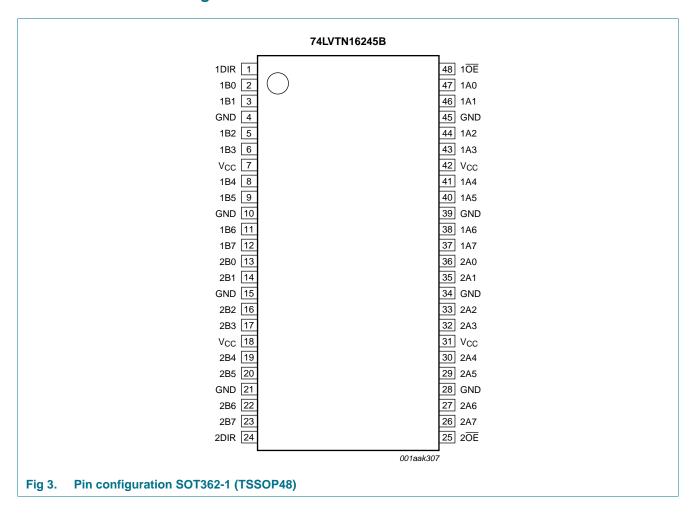
4. Functional diagram

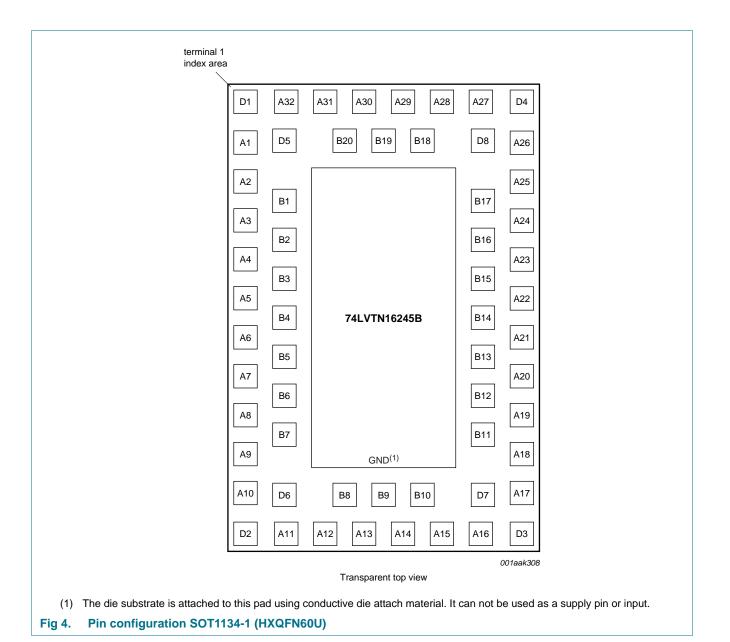




5. Pinning information

5.1 Pinning





74LVTN16245B

5.2 Pin description

Table 2. Pin description

Symbol	Pin		Description
	SOT362-1	SOT1134-1	
1DIR, 2DIR	1, 24	A30, A13	direction control input
1B0 to 1B7	2, 3, 5, 6, 8, 9, 11, 12	B20, A31, D5, D1, A2, B2, B3, A5	data input/output
2B0 to 2B7	13, 14, 16, 17, 19, 20, 22, 23	A6, B5, B6, A9, D2, D6, A12, B8	data input/output
GND	4, 10, 15, 21, 28, 34, 39, 45	A32, A3, A8, A11, A16, A19, A24, A27	ground (0 V)
V _{CC}	7, 18, 31, 42	A1, A10, A17, A26	supply voltage
10E, 20E	48, 25	A29, A14	output enable input (active LOW)
2A0 to 2A7	36, 35, 33, 32, 30, 29, 27, 26	A21, B13, B12, A18, D3, D7, A15, B10	data input/output
1A0 to 1A7	47, 46, 44, 43, 41, 40, 38, 37	B18, A28, D8, D4, A25, B16, B15, A22	data input/output
n.c.	-	A4, A7, A20, A23, B1, B4, B7, B9, B11, B14, B17, B19	not connected

6. Functional description

Table 3. Function table [1]

Control		Input/output				
nOE	nDIR	nAn	nBn			
L	L	output nAn = nBn	input			
L	Н	input	output nBn = nAn			
Н	X	Z	Z			

^[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+4.6	V
VI	input voltage		<u>[1]</u> –0.5	+7.0	V
Vo	output voltage	output in OFF-state or HIGH-state	[<u>1</u>] -0.5	+7.0	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
I _O	output current	output in LOW-state	-	128	mA
		output in HIGH-state	-64	-	mA
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		[2] -	150	°C

74LVTN16245B

All information provided in this document is subject to legal disclaimers.

Table 4. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
P_{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C}$ to +85 $^{\circ}\text{C}$			
		TSSOP48 package	<u>[3]</u> _	500	mW
		HXQFN60U package	<u>[4]</u> _	1000	mW

^[1] The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CC}	supply voltage		2.7	-	3.6	V
VI	input voltage		0	-	5.5	V
V _{IH}	HIGH-level input voltage		2.0	-	-	V
V _{IL}	LOW-level input voltage		-	-	0.8	V
I _{OH}	HIGH-level output current		-32	-	-	mA
I _{OL}	LOW-level output current	none	-	-	32	mA
		current duty cycle \leq 50 %; $f_i \geq$ 1 kHz	-	-	64	mA
T _{amb}	ambient temperature	in free-air	-40	-	+85	°C
Δt/ΔV	input transition rise and fall rate	outputs enabled	-	-	10	ns/V

9. Static characteristics

Table 6. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ[1]	Max	Unit
$T_{amb} = -4$	40 °C to +85 °C					
V_{IK}	input clamping voltage	$V_{CC} = 2.7 \text{ V}; I_{IK} = -18 \text{ mA}$	-1.2	-0.85	-	V
V_{OH}	HIGH-level output voltage	$I_{OH} = -100 \mu A$; $V_{CC} = 2.7 \text{ V to } 3.6 \text{ V}$	$V_{CC}-0.2$	V_{CC}	-	V
		$I_{OH} = -8 \text{ mA}; V_{CC} = 2.7 \text{ V}$	2.4	2.5	-	V
		$I_{OH} = -32 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.0	2.3	-	V
V _{OL} I	LOW-level output voltage	V _{CC} = 2.7 V				
		I _{OL} = 100 μA	-	0.07	0.2	V
		I _{OL} = 24 mA	-	0.3	0.5	V
		V _{CC} = 3.0 V				
		I _{OL} = 16 mA	-	0.25	0.4	V
		I _{OL} = 32 mA	-	0.3	0.5	V
		I _{OL} = 64 mA	-	0.4	0.55	V

74LVTN16245B

All information provided in this document is subject to legal disclaimers.

^[2] The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability.

^[3] Above 60 °C the value of Ptot derates linearly with 5.5 mW/K.

^[4] Above 70 °C the value of P_{tot} derates linearly with 1.8 mW/K.

 Table 6.
 Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ[1]	Max	Unit
l _l	input leakage current	control pins				
		$V_{CC} = 3.6 \text{ V}; V_I = V_{CC} \text{ or GND}$	-	0.1	±1	μΑ
		$V_{CC} = 0 \text{ V or } 3.6 \text{ V}; V_{I} = 5.5 \text{ V}$	-	0.1	10	μΑ
		input/output data pins; V _{CC} = 3.6 V	[2]			
		V _I = 5.5 V	-	0.1	20	μΑ
		$V_I = V_{CC}$	-	0.5	10	μΑ
		V _I = 0 V	-5	-0.1	-	μΑ
I _{OFF}	power-off leakage current	$V_{CC} = 0 \text{ V}$; V_{I} or $V_{O} = 0 \text{ V}$ to 4.5 V	-	0.1	±100	μΑ
I _{LO}	output leakage current	output in HIGH-state when $V_O > V_{CC}$; $V_O = 5.5 \text{ V}$; $V_{CC} = 3.0 \text{ V}$	-	75	125	μА
I _{O(pu/pd)}	power-up/power-down output current	$V_{CC} \le 1.2 \text{ V}; V_O = 0.5 \text{ V} \text{ to } V_{CC};$ $V_I = \text{GND or } V_{CC}; n\overline{\text{OE}} = \text{don't care}$	[3]	40	±100	μА
I _{CC}	supply current	V_{CC} = 3.6 V; V_I = GND or V_{CC} ; I_O = 0 A				
		output HIGH	-	0.07	0.12	mΑ
		output LOW	-	4.0	6.0	mΑ
		outputs disabled	[4] _	0.07	0.12	mΑ
Δl _{CC}	additional supply current	per input pin; V_{CC} = 3.0 V to 3.6 V; one input at V_{CC} – 0.6 V other inputs at V_{CC} or GND	<u>[5]</u> _	0.1	0.2	mA
Cı	input capacitance	pins nDIR and n \overline{OE} , V _O = 0 V or 3.0 V	-	3	-	pF
$C_{io(off)}$	off-state input/output capacitance	pins nAn and nBn, outputs disabled; $V_O = \text{GND}$ or V_{CC}	-	9	-	pF

^[1] Typical values are measured at $V_{CC} = 3.3 \text{ V}$ and at $T_{amb} = 25 \,^{\circ}\text{C}$.

^[2] Unused pins at V_{CC} or GND.

^[3] This parameter is valid for any V_{CC} between 0 V and 1.2 V with a transition time of up to 10 ms. From V_{CC} = 1.2 V to V_{CC} = 3.3 V \pm 0.3 V a transition time of 100 μ s is permitted. This parameter is valid for T_{amb} = 25 °C only.

^[4] I_{CC} is measured with outputs pulled to V_{CC} or GND.

^[5] This is the increase in supply current for each input at the specified voltage level other than V_{CC} or GND.

10. Dynamic characteristics

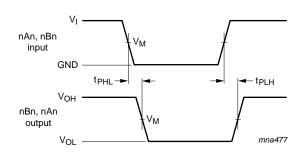
Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7.

Symbol	Parameter	Conditions	Min	Typ <mark>[1]</mark>	Max	Unit
$T_{amb} = -40$	°C to +85 °C					
t _{PLH}	LOW to HIGH propagation delay	nAn to nBn or nBn to nAn; see <u>Figure 5</u>				
		V _{CC} = 2.7 V	-	-	3.5	ns
		V _{CC} = 3.0 V to 3.6 V	1.0	1.9	3.3	ns
t _{PHL}	HIGH to LOW propagation delay	nAn to nBn or nBn to nAn; see Figure 5				
		V _{CC} = 2.7 V	-	-	3.5	ns
		V _{CC} = 3.0 V to 3.6 V	1.0	1.7	3.3	ns
t _{PZH}	OFF-state to HIGH propagation delay	nOE to nAn or nBn; see <u>Figure 6</u>				
		V _{CC} = 2.7 V	-	-	5.3	ns
		V _{CC} = 3.0 V to 3.6 V	1.0	2.8	4.5	ns
t _{PZL}	OFF-state to LOW propagation delay	nOE to nAn or nBn; see <u>Figure 6</u>				
		V _{CC} = 2.7 V	-	-	5.1	ns
		$V_{CC} = 3.0 \text{ V to } 3.6 \text{ V}$	1.0	2.8	4.1	ns
t _{PHZ}	HIGH to OFF-state propagation delay	nOE to nAn or nBn; see Figure 6				
		V _{CC} = 2.7 V	-	-	5.7	ns
		V _{CC} = 3.0 V to 3.6 V	1.5	3.2	5.1	ns
t _{PLZ}	LOW to OFF-state propagation delay	nOE to nAn or nBn; see Figure 6				
		V _{CC} = 2.7 V	-	-	4.6	ns
		V _{CC} = 3.0 V to 3.6 V	1.5	3.0	4.6	ns

^[1] Typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 $^{\circ}C.$

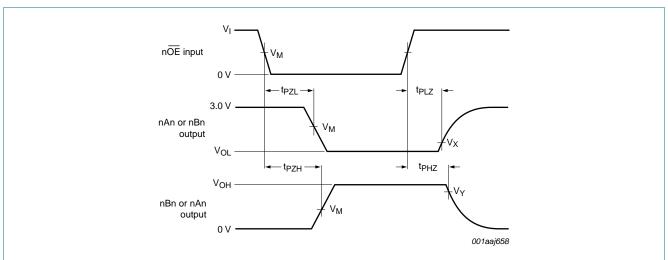
11. Waveforms



Measurements points are given in <u>Table 8</u>.

 V_{OL} and V_{OH} are typical voltage output levels that occur with the output load.

Fig 5. Propagation delay input (nAn, nBn) to output (nBn, nAn)



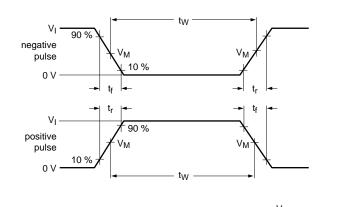
Measurements points are given in Table 8.

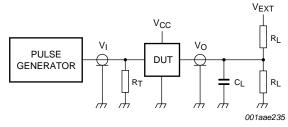
 $\ensuremath{V_{OL}}$ and $\ensuremath{V_{OH}}$ are typical voltage output levels that occur with the output load.

Fig 6. Enable and disable times

Table 8. Measurement points

Input	Output		
V_{M}	V _M	V _X	V _Y
1.5 V	1.5 V	V _{OL} + 0.3 V	$V_{OH} - 0.3 V$





Test data is given in Table 9.

Definitions test circuit:

 R_L = Load resistance.

 C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

 V_{EXT} = External voltage for measuring switching times.

Fig 7. Load circuit for measuring switching times

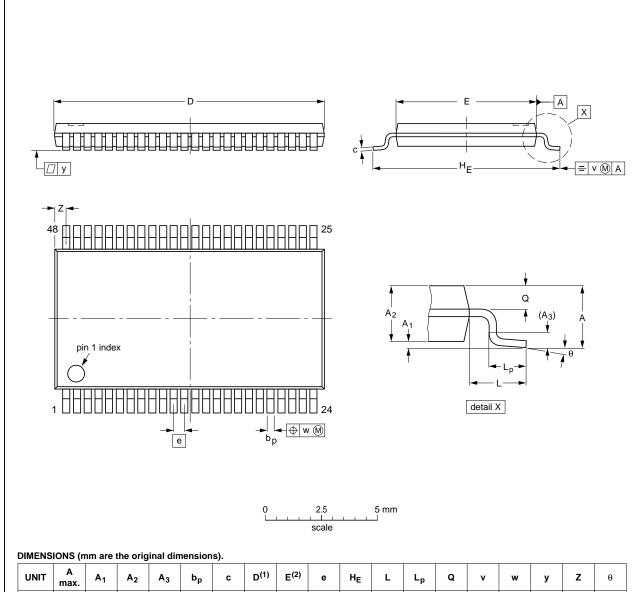
Table 9. Test data

Input				Load		V _{EXT}			
V_{I}	f _i	t _W	t _r , t _f	CL	R_L	t _{PHZ} , t _{PZH}	t_{PLZ} , t_{PZL}	t _{PLH} , t _{PHL}	
2.7 V	≤ 10 MHz	500 ns	≤ 2.5 ns	50 pF	500Ω	GND	6 V	open	

12. Package outline

TSSOP48: plastic thin shrink small outline package; 48 leads; body width 6.1 mm

SOT362-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽²⁾	е	HE	L	Lp	Q	v	w	у	Z	θ
mm	1.2	0.15 0.05	1.05 0.85	0.25	0.28 0.17	0.2 0.1	12.6 12.4	6.2 6.0	0.5	8.3 7.9	1	0.8 0.4	0.50 0.35	0.25	0.08	0.1	0.8 0.4	8° 0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN	ISSUE DATE
	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT362-1		MO-153				99-12-27 03-02-19

Fig 8. Package outline SOT362-1 (TSSOP48)

74LVTN16245B All information provided in this document is subject to legal disclaimers.

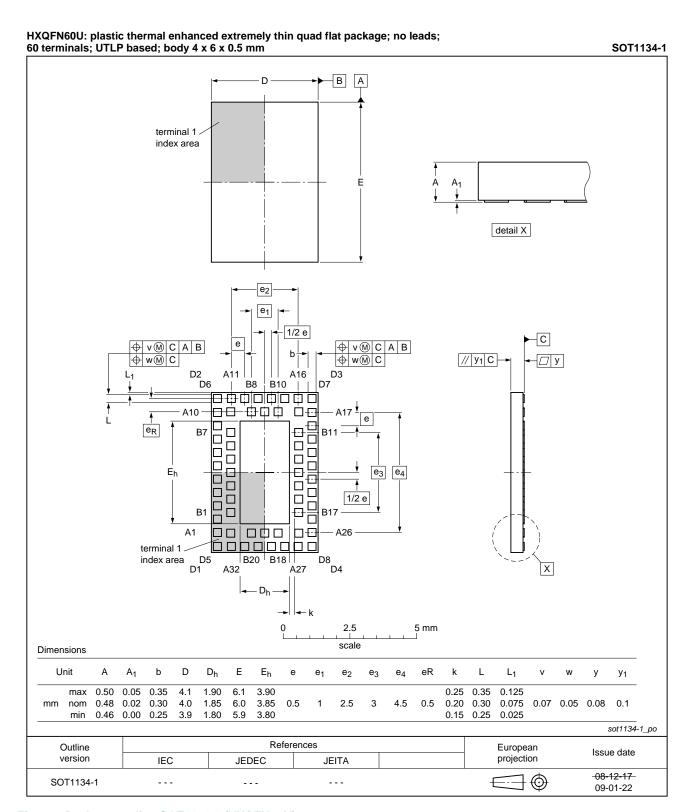


Fig 9. Package outline SOT1134-1 (HXQFN60U)

74LVTN16245B

All information provided in this document is subject to legal disclaimers.

13. Abbreviations

Table 10. Abbreviations

Acronym	Description
BiCMOS	Bipolar Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVTN16245B v.3	20110615	Product data sheet	-	74LVTN16245B v.2
Modifications:	• 74LVTN162	45BBQ changed to 74LVT	N16245BBX for HXQFN	60U (SOT1134-1) package.
74LVTN16245B v.2	20100323	Product data sheet	-	74LVTN16245B v.1
Modifications:	 74LVTN162 package. 	45BBQ changed from HU0	QFN60U (SOT1025-1) to	HXQFN60U (SOT1134-1)
74LVTN16245B v.1	20090729	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

15.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Product specification — The information and data provided in a Product data sheet shall define the specification of the product as agreed between NXP Semiconductors and its customer, unless NXP Semiconductors and customer have explicitly agreed otherwise in writing. In no event however, shall an agreement be valid in which the NXP Semiconductors product is deemed to offer functions and qualities beyond those described in the Product data sheet.

15.3 Disclaimers

Limited warranty and liability — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

In no event shall NXP Semiconductors be liable for any indirect, incidental, punitive, special or consequential damages (including - without limitation - lost profits, lost savings, business interruption, costs related to the removal or replacement of any products or rework charges) whether or not such damages are based on tort (including negligence), warranty, breach of contract or any other legal theory.

Notwithstanding any damages that customer might incur for any reason whatsoever, NXP Semiconductors' aggregate and cumulative liability towards customer for the products described herein shall be limited in accordance with the *Terms and conditions of commercial sale* of NXP Semiconductors.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use in automotive applications — This NXP Semiconductors product has been qualified for use in automotive applications. The product is not designed, authorized or warranted to be

suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Customers are responsible for the design and operation of their applications and products using NXP Semiconductors products, and NXP Semiconductors accepts no liability for any assistance with applications or customer product design. It is customer's sole responsibility to determine whether the NXP Semiconductors product is suitable and fit for the customer's applications and products planned, as well as for the planned application and use of customer's third party customer(s). Customers should provide appropriate design and operating safeguards to minimize the risks associated with their applications and products.

NXP Semiconductors does not accept any liability related to any default, damage, costs or problem which is based on any weakness or default in the customer's applications or products, or the application or use by customer's third party customer(s). Customer is responsible for doing all necessary testing for the customer's applications and products using NXP Semiconductors products in order to avoid a default of the applications and the products or of the application or use by customer's third party customer(s). NXP does not accept any liability in this respect.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) will cause permanent damage to the device. Limiting values are stress ratings only and (proper) operation of the device at these or any other conditions above those given in the Recommended operating conditions section (if present) or the Characteristics sections of this document is not warranted. Constant or repeated exposure to limiting values will permanently and irreversibly affect the quality and reliability of the device.

Terms and conditions of commercial sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, unless otherwise agreed in a valid written individual agreement. In case an individual agreement is concluded only the terms and conditions of the respective agreement shall apply. NXP Semiconductors hereby expressly objects to applying the customer's general terms and conditions with regard to the purchase of NXP Semiconductors products by customer.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

74LVTN16245B

All information provided in this document is subject to legal disclaimers.

74LVTN16245B

3.3 V 16-bit transceiver; 3-state

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

15.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

16. Contact information

For more information, please visit: http://www.nxp.com

For sales office addresses, please send an email to: salesaddresses@nxp.com

17. Contents

1	General description
2	Features and benefits
3	Ordering information 1
4	Functional diagram 2
5	Pinning information 4
5.1	Pinning
5.2	Pin description 6
6	Functional description 6
7	Limiting values 6
8	Recommended operating conditions 7
9	Static characteristics 7
10	Dynamic characteristics 9
11	Waveforms
12	Package outline
13	Abbreviations
14	Revision history
15	Legal information
15.1	Data sheet status
15.2	Definitions
15.3	Disclaimers
15.4	Trademarks16
16	Contact information 16
17	Contents

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.